

Features

- Low capacitance
- Low leakage current



DFN1006



Schematic Diagram

Applications

- Tablets, eReaders
- External storage
- Ultrabooks, Notebooks
- High speed serial interfaces

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Power Dissipation (T _p =8/20μS)	P _{PK}	54	W
ESD per IEC 61000-4-2 (Air)	V _{ESD}	±30	kV
ESD per IEC 61000-4-2 (Contact)			
Peak Pulse Current (T _p =8/20μS)	I _{PP}	3	A
Operation Junction Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Stand-Off Voltage	V _{RWM}	-	-	-	5.3	V
Reverse Breakdown Voltage	V _{(BR)R}	I _R =1mA	6.8	-	9	V
Reverse Current	I _R	V _R =5.3V	-	-	100	nA
Clamping Voltage	V _C	I _{PP} =1A, t _p =8/20μs	-	-	13	V
		I _{PP} =3A, t _p =8/20μs	-	-	18	V
Clamping Voltage	V _{CL}	I _{TLP} =4A, t _p =0.2/100ns	-	18.2	-	V
		I _{TLP} =16A, t _p =0.2/100ns	-	38.9	-	V
Junction Capacitance	C _J	V _R =0V, F=1MHz	-	0.25	-	pF
Dynamic Resistance ¹	R _{DYN}	-	-	1.7	-	Ω

Note:

1. Dynamic Resistance calculated from I_{TLP}=4A to I_{TLP}=16A .

Electrical Characteristic Curves

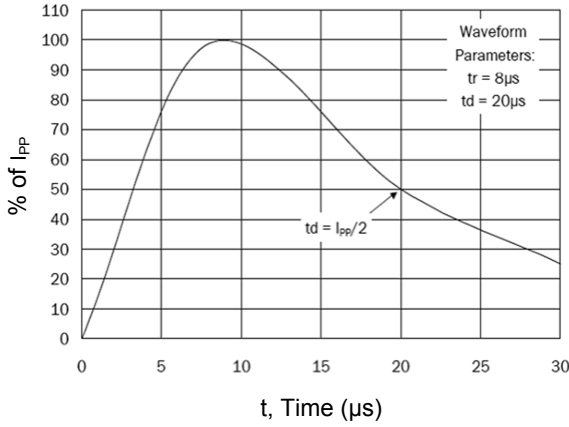


Figure 1. Pulse Waveform

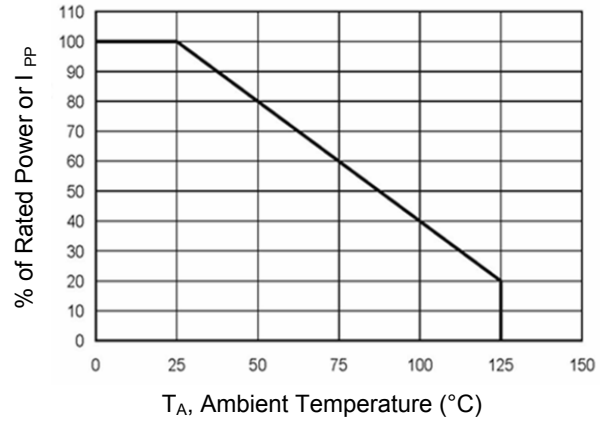


Figure 2. Power Derating Curve

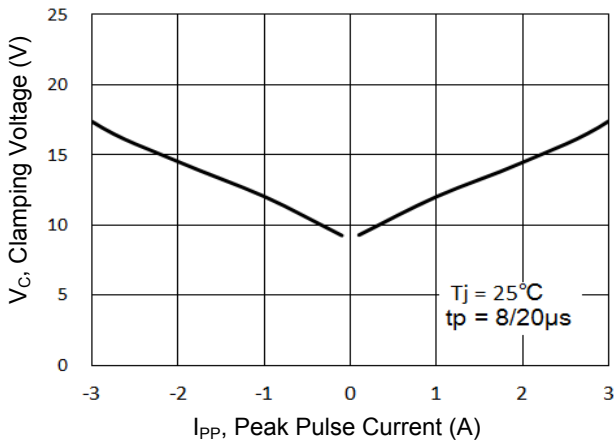


Figure 3. Clamping Voltage Curve

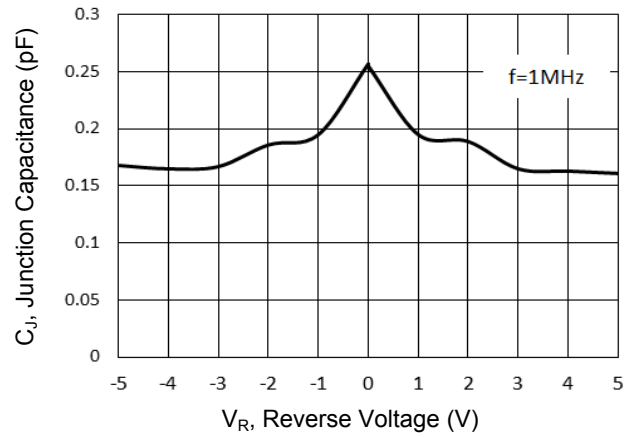


Figure 4. Junction Capacitance

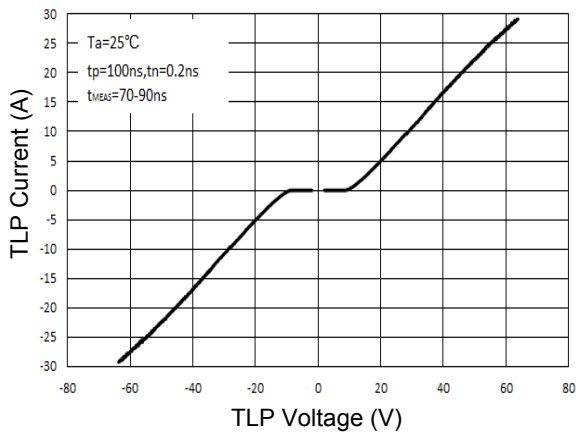
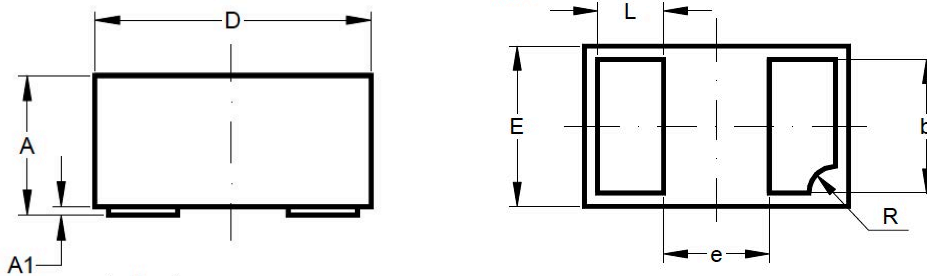


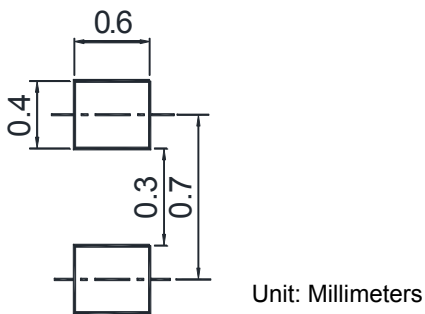
Figure 5. TLP Curve

Package Outline Dimensions (DFN1006)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.460	0.510	0.018	0.020
A1	0.000	0.050	0.000	0.002
b	0.450	0.550	0.018	0.022
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
e	0.400		0.016	
L	0.200	0.300	0.008	0.012
R	0.050	0.150	0.002	0.006

Recommended Pad Layout



Order Information

Device	Package	Marking	Carrier	Quantity
GSEZ5B025	DFN1006	7T	Tape & Reel	10,000pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com